

## References

- [1] N. Sengouga, Hole traps in GaAs FETs : characterization and backgating effects, Phd thesis, Lancaster university (1991)
- [2] C.N. Graham, Novel measurements of Defects in Field Effect Transistors, Phd thesis, Lancaster university (2002)
- [3] P. Gurry, The Kink effect in GaAS power MESFETs, Master thesis, Lancaster university (1996)
- [4] M. Snowden Christopher, Introduction to semiconductor device Modelling, World Scientific Publication, Singapore (1986)
- [5] V.O. Katai and B. K. Jones. Solid-State Electron. Vol. 30. 897 (1987)
- [6] H.J. Queisser, Proceedings of ESSDERC 1972, IOP Conference Series No. 15 (IOP, London, 1972), pp. 145-88 (1972)
- [7] M. Kurata, Numerical Analysis for Semiconductor Devices, Lexington Books, Lexington, Massachusetts. Toronto (1982).
- [8] HK. Gummel, A self consistent iterative scheme for one dimensional steady state transistor calculation, IEEE Trans. Electron devices, ED-11,pp.455-465 (1964)
- [9] J.W. Slotboom, Iterative scheme for 1- and 2- dimensional DC transistor simulation, Electron. Lett.;5,677-678,1969
- [10] DL. Scharfeter, and HK. Gummel, Large signal analysis of silicon Read diode oscillator; IEEE Trans. Electron devices, ED-16, pp.64-77 (1969)
- [11] VM Goldshmidt, Tran. Faraday soc.25.253 (1929)
- [12] K. Ohata, H. Itoth , F. Hasegawa Jpn. J. Appl. Phys. 19. 357 (1979)
- [13] GL. Miller, DV. Lang, LC. Kimerling , Ann. Rev. Mat. Sci.7.377 (1977)
- [14] CT. Sah, RN. Noyce, Shockley. Proc. IRE45, 1228 (1975)
- [15] W. Shockley, WT. Read, Phys. Rev. 87, 835 (1952)
- [16] RN. Hall, Phys. Rev.87, 387 (1952)
- [17] DC. D'avanzo , IEEE Trans. Electron Dev.ED-29,1051-1059 (1982)
- [18] WM. Paulson, NS. Birrittella, TH. Miers and KL. Mc Laughlin, IEEE GaAs IC Symp. 166-167 (1982)

- [19] A. Mitonneau, GM. Martin, A. Mircea, Electronics letters 13, 666 (1977)
- [20] GM. Martin, A. Mitonneau, A. Mircea, Electronics letters 13, 191(1977)
- [21] HJ. Quiesser , J. Appl. Phys.43 3892 (1972)
- [22] DVJ. Lang, Appl. Phys. 45, 3014 (1974)
- [23] CP. Lee, SJ. Lee and BM. Welch, IEEE Electron Dev. Lett. EDL-3 97-98(1982)
- [24] MA. Lampert and P. Mark ,“ Current injection in solids” Academic Press (New York) (1970)
- [25] Van Roosbroeck, Phys. Rev. 123, 474 (1961)
- [26] R. Pucel, HA. Haus, H. Statz,“ Advances in Electron Physics 38”, Academic Press (New York) (1975)
- [27] M. Shur , “ GaAs Devices and circuits”, Plenum Press , New York (1989)
- [28] W. Shockley , Proc. IRE 40, 1365 (1952)
- [29] W. Van Roosbroeck and HC. Casy , Phys. Rev. B 5 2154 (1972) Jr
- [30] W. Shockley, Electron and holes in semiconductors, Princeton: Van Nostrand. (1950)
- [31] W E. Philips and J R. Lowney. Appl. Phys. 54 2786-2791(1983 )
- [32] SM. Sze, Physics of semiconductor Devices, (2<sup>nd</sup> edition ) J. Wiley & Sons , New York (1981)
- [33] B. Tuck, GA. Adegboyega , Jay RP and Cardwell M J, Inst. Phys. Conf. Ser. No.45 114-124 (1979)
- [34] CA. Liechti ,IEEE Trans. Microw. Theory Techni. MTT-24 279-300 (1976)
- [35] P.K. Bhattacharya and S. Dhar, semiconductors and semimetals 26 Academic press (New York) 143-228 (1988)
- [36] J. Bourgoin and M. Lanoo, “Point Defects in Semiconductors II: Experimental Aspects ” Springer (Berlin) ( 1983)
- [37] D. Goguenheim and M. Lanoo, J. Appl. Phys. 68 1059-1069 (1990)
- [38] J. Barrera, Proc.5<sup>th</sup> Bienn. Cornell Electrical Eng. Conf. 135-144 (1975)
- [39] H. Grononkin, MS. Birrittella, WC. Seelbach and RL. Vaitkus, IEEE Trans. Electron Dev. ED-29 845-850 (1982)

- [40] MS. Birrittella, WC. Seelbach and RL. Vaitkus, IEEE Trans. Electron Dev. ED-29 1135-1142 (1982)
- [41] C. Kocot and CA. Stolte, IEEE Trans. Microw. Theor. Techni. MTT-30 963-968 (1982)
- [42] SR. Bligth and H. Thomas GEC J. Res. 6 25-36 (1988)
- [43] WS. Lee, Electron. Lett. 23 587-589 (1987)
- [44] N. Sengouga, B.K. Jones, Solid State Electronics, Vol. 38, No. 7, pp.1413-1421(1995)
- [45] WS. Lee, Ins. Phys. Conf. Ser. No. 91 773-776 (1988)
- [46] WB. liegh, JS. Blakemore, and RY. Koyama, IEEE Trans. Electron Dev. ED-32 1835-1841(1985)
- [47] S. Makrem- Ebied and P. Mimondo, IEEE Trans. Electron Dev. ED-32 632-642 (1985)
- [48] ST. Fu and MB. Das, IEEE Trans. Electron Dev. ED-34 1245-1252 (1987)
- [49] GJ. Papaioannou,J. Kaliakatsos, JR. Forrest and PC. Euthymiou, Inst. Phys. Conf. Ser. No. 91 733-736 (1988)
- [50] H. Itoh, K. Ohata and F. Hasegawa, IEEE Trans. Electron Dev. ED-28 876-882 (1981)
- [51] T. Nozaki, M.Ogawa, H. Terao and H. Watanable, Inst. Phys. Conf. Ser. No. 24 46-54 (1975)
- [52] N. Yokoyama, A. Shibatomi, S. Ohkawa, M. Fukuta and H. Ishikawa, Inst. Phys. Conf. Ser. No 33b 201-209 (1977)
- [53] T. Itoh and H. Yani, Inst. Phys. Conf. Ser. No.45 326-334 (1979)
- [54] T. Itoh and H. Yani, Proc.11<sup>th</sup> Inst. Phys. Conf. Sol. State Dev, Tokyo, 351-355 (1979)
- [55] K. Yamasaki, N. Kato and M. Hirayama, IEEE Trans. Electron Dev. ED-32 2420-2425 (1985)
- [56] CL. Chen, FW. Smith, AR. Calawa, LJ. Mahoney and MJ. Manfra, IEEE Trans. Electron Dev. ED-36 1546-1556 (1989)
- [57] MR. Melloch, DC. Miller and B. Das, Appl. Phys. Lett. 54 943-945 (1989)